

NOT RECOMMENDED FOR NEW DESIGN **USE FZT788B**

LOW V_{CE(SAT)} PNP SURFACE MOUNT TRANSISTOR



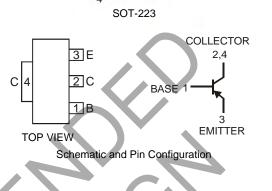
3

Features

- **Epitaxial Planar Die Construction** .
- Low Collector-Emitter Saturation Resistance $R_{CE(SAT)} = 70m\Omega$ at 3A •
- High DC Current Gain h_{FE} > 300 at I_C = 2A
- Complementary NPN Type Available (DNLS412E)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-223 •
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.112 grams (approximate)



Maximum Ratings @T_A = 25°C unless otherwise specified

| Characteristic | | Symbol | Value | Unit |
|------------------------------|--|------------------|-------|------|
| Collector-Base Voltage | | V _{CBO} | -15 | V |
| Collector-Emitter Voltage | | V _{CEO} | -15 | V |
| Emitter-Base Voltage | | V _{EBO} | -5 | V |
| Continuous Collector Current | | lc | -3 | A |
| Peak Pulse Current | | I _{CM} | -8 | А |
| | | | | |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|---|-----------------------------------|-------------|------|
| Power Dissipation @ $T_A = 25^{\circ}C$ (Note 3) | PD | 1 | W |
| Thermal Resistance, Junction to Ambient Air (Note 1) $@T_A = 25^{\circ}C$ | R _{0JA} | 125 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Notes: 1. No purposefully added lead.

2. Diodes Inc s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

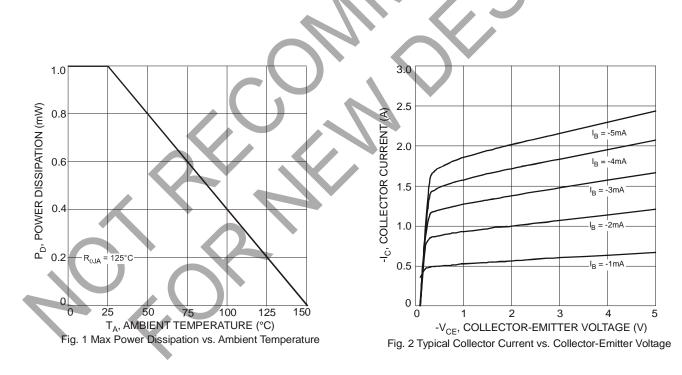
3. Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Electrical Characteristics @T_A = 25°C unless otherwise specified

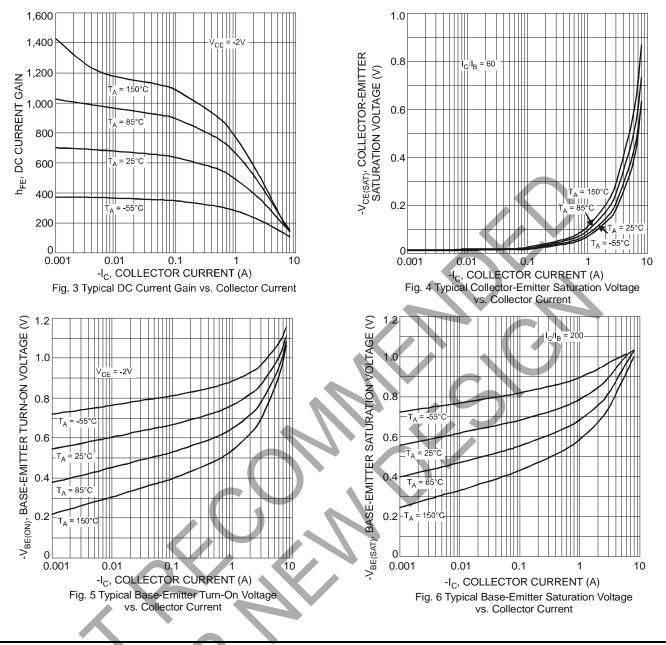
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|--------------------------------------|-------------------------------------|--------------------------|----------------------------------|---------------------------------|----------|--|
| OFF CHARACTERISTICS (Note 4) | | | | · | · | · |
| Collector-Base Breakdown Voltage | V _{(BR)CBO} | -15 | — | _ | V | $I_{\rm C} = -100 \mu A, I_{\rm E} = 0$ |
| Collector-Emitter Breakdown Voltage | V _{(BR)CEO} | -15 | _ | _ | V | $I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0$ |
| Emitter-Base Breakdown Voltage | V _{(BR)EBO} | -5 | _ | _ | V | $I_E = -100 \mu A$, $I_C = 0$ |
| Collector Cutoff Current | I _{CBO} | _ | _ | -0.1 | μΑ | $V_{CB} = -10V, I_E = 0$ |
| Emitter Cutoff Current | I _{EBO} | | — | -0.1 | μA | $V_{EB} = -4V, I_{C} = 0$ |
| ON CHARACTERISTICS (Note 4) | | | | | | • |
| Collector-Emitter Saturation Voltage | V _{CE(SAT)} | _ | -0.08 -0.12 -0.22 -0.21 | -0.15 -0.25 -0.45 -0.5 | v | $I_{C} = -0.5A, I_{B} = -2.5mA$ $I_{C} = -1A, I_{B} = -5mA$ $I_{C} = -2A, I_{B} = -10mA$ $I_{C} = -3A, I_{B} = -50mA$ |
| Base-Emitter Saturation Voltage | V _{BE(SAT)} | _ | _ | -0.9 | V | I _C = -1A, I _B = -5mA |
| Base-Emitter Turn-On Voltage | V _{BE(ON)} | | -0.75 | | V | $V_{CE} = -2V, I_{C} = -1A$ |
| DC Current Gain | h _{FE} | 500 400 300 150 | | 1500 | F | V _{CE} = -2V, I _C = -10mA V _{CE} = -2V, I _C = -1A V _{CE} = -2V, I _C = -2A V _{CE} = -2V, I _C = -6A |
| AC CHARACTERISTICS | | | | | | |
| Transition Frequency | f⊤ | 100 | | | MHz | $V_{CE} = -5V$, $I_C = -50mA$, f = 50MHz |
| Input Capacitance | Cibo | | 245 | | MHz | V _{EB} = -0.5V, f = 1MHz |
| Output Capacitance | C _{obo} | - | 45 | <u> </u> | pF | V _{CB} = -10V, f = 1MHz |
| Switching Times | t _{on} t _{off} | | 35 200 | _ | ns ns | $V_{CC} = -10V$, $I_C = -500mA$, $I_{B1} = -I_{B2} = -50mA$ |

Notes: 4. Pulse Test: Pulse width \leq 300 μ s. Duty cycle \leq 2.0%.





NOT RECOMMENDED FOR NEW DESIGN USE FZT788B

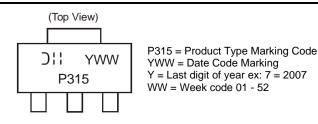


Ordering Information (Note 5)

| Device | Packaging | Shipping |
|-------------|-----------|------------------|
| DPLS315E-13 | SOT-223 | 2500/Tape & Reel |

Notes: 5. For packaging details, please go to our website at http://www.diodes.com/ap02007.pdf.

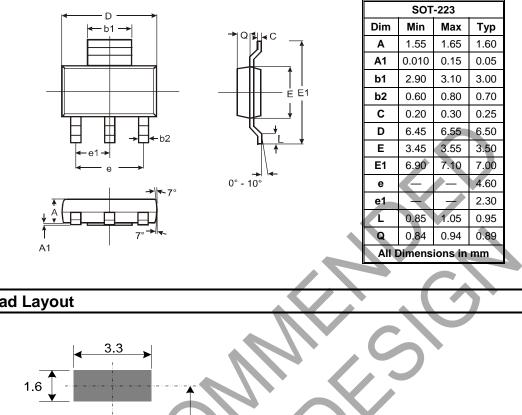
Marking Information



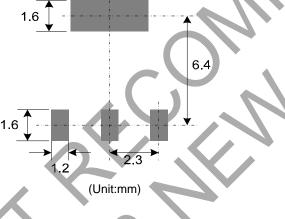
DS31325 Rev. 4 - 3



Package Outline Dimensions



Suggested Pad Layout



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